

ABSTRACT OF THE DISCLOSURE

In a semiconductor light emitting device including a mesa section having at least a sandwich structure of an n-type clad layer, an active layer and a p-type clad layer which are constituted by compound semiconductor layers formed on a substrate, and an inorganic insulating film 22 formed to cover the mesa section excluding a contact region, the inorganic insulating film is constituted by an inorganic insulating film having a vacancy rate of 50% or more.